

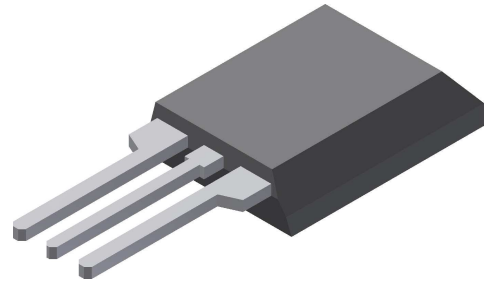
HiPerFRED

$V_{RRM} = 2 \times 600 \text{ V}$
 $I_{FAV} = 15 \text{ A}$
 $t_{rr} = 25 \text{ ns}$

High Performance Fast Recovery Diode
 Low Loss and Soft Recovery
 Phase leg

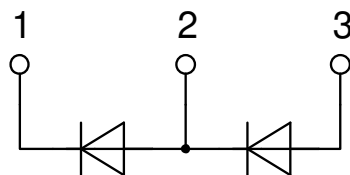
Part number

DSEE15-12CC



Backside: isolated

 E72873



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: ISOPLUS220

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

Disclaimer Notice

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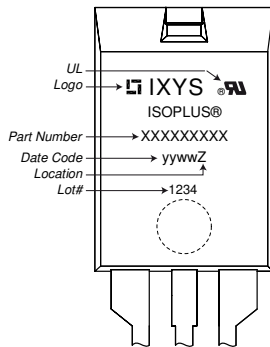


Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage					600	V
V_{RRM}	max. repetitive reverse blocking voltage					600	V
I_R	reverse current, drain current	$V_R = 600\text{ V}$		$T_{VJ} = 25^\circ\text{C}$		100	μA
		$V_R = 600\text{ V}$		$T_{VJ} = 150^\circ\text{C}$		0.5	mA
V_F	forward voltage drop	$I_F = 15\text{ A}$		$T_{VJ} = 25^\circ\text{C}$		2.04	V
		$I_F = 30\text{ A}$				2.25	V
		$I_F = 15\text{ A}$		$T_{VJ} = 150^\circ\text{C}$		1.35	V
		$I_F = 30\text{ A}$				1.59	V
I_{FAV}	average forward current	$T_C = 140^\circ\text{C}$	rectangular	$T_{VJ} = 175^\circ\text{C}$		15	A
V_{FO}	threshold voltage	} for power loss calculation only		$T_{VJ} = 175^\circ\text{C}$		0.99	V
r_F	slope resistance					15	m Ω
R_{thJC}	thermal resistance junction to case					1.6	K/W
R_{thCH}	thermal resistance case to heatsink				0.5		K/W
P_{tot}	total power dissipation			$T_C = 25^\circ\text{C}$		95	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}; V_R = 0\text{ V}$		$T_{VJ} = 45^\circ\text{C}$		110	A
C_J	junction capacitance	$V_R = 400\text{ V}$ $f = 1\text{ MHz}$		$T_{VJ} = 25^\circ\text{C}$		12	pF
I_{RM}	max. reverse recovery current	} $I_F = 15\text{ A}; V_R = 300\text{ V}$		$T_{VJ} = 25^\circ\text{C}$		11	A
				$T_{VJ} = 100^\circ\text{C}$		19	A
t_{rr}	reverse recovery time	} $-di_F/dt = 600\text{ A}/\mu\text{s}$		$T_{VJ} = 25^\circ\text{C}$		25	ns
				$T_{VJ} = 100^\circ\text{C}$		83	ns



Package ISOPLUS220		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			35	A
T_{VJ}	virtual junction temperature		-55		175	°C
T_{op}	operation temperature		-55		150	°C
T_{stg}	storage temperature		-55		150	°C
Weight				2		g
F_C	mounting force with clip		20		60	N
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	1.0			mm
$d_{Spb/Apb}$		terminal to backside	3.0			mm
V_{ISOL}	isolation voltage	t = 1 second t = 1 minute	3600 3000			V V
		50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA				

Product Marking



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEE15-12CC	DSEE15-12CC	Tube	50	500725

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 175^{\circ}C$

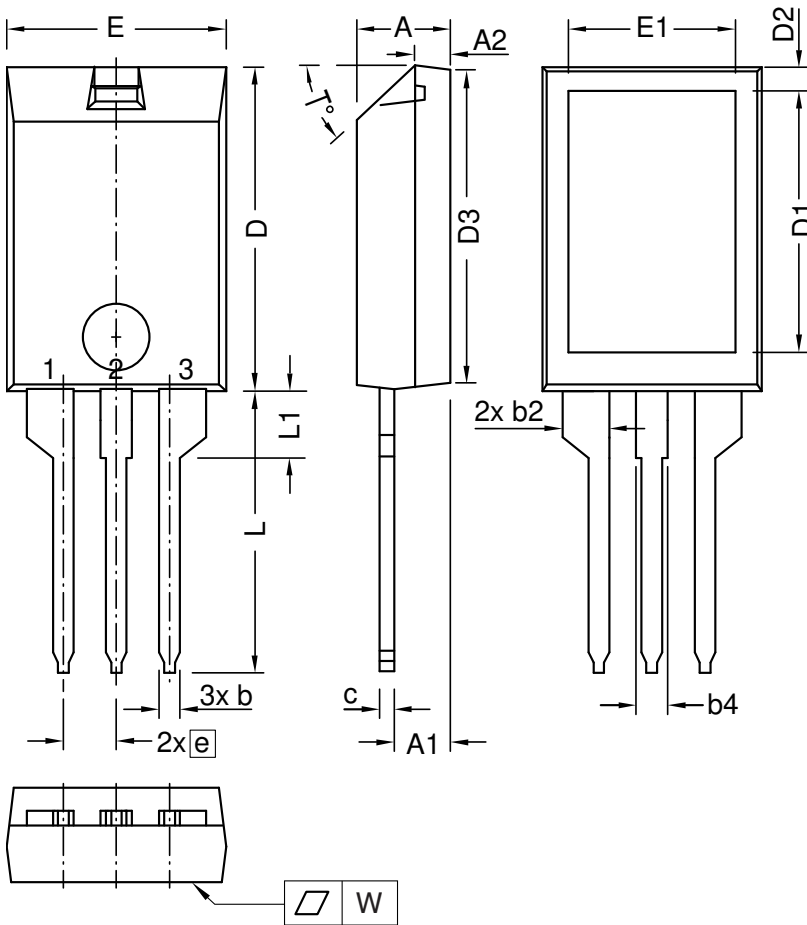


Fast Diode

$V_{0\ max}$	threshold voltage	0.99	V
$R_{0\ max}$	slope resistance *	11.3	mΩ



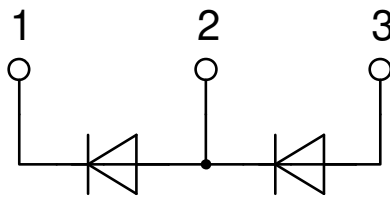
Outlines ISOPLUS220



Dim.	Millimeters		Inches	
	min	max	min	max
A	4.00	5.00	0.157	0.197
A1	2.50	3.00	0.098	0.118
A2	1.60	1.80	0.063	0.071
b	0.90	1.30	0.035	0.051
b2	2.35	2.55	0.093	0.100
b4	1.25	1.65	0.049	0.065
c	0.70	1.00	0.028	0.039
D	15.00	16.00	0.591	0.630
D1	12.00	13.00	0.472	0.512
D2	1.10	1.50	0.043	0.059
D3	14.90	15.50	0.587	0.610
E	10.00	11.00	0.394	0.433
E1	7.50	8.50	0.295	0.335
e	2.54 BSC		0.100 BSC	
L	13.00	14.50	0.512	0.571
L1	3.00	3.50	0.118	0.138
T°	42.5	47.5		
W	-	0.1	-	0.004

Die konvexe Form des Substrates ist typ. < 0.04 mm über der Kunststoffoberfläche der Bauteilunterseite
The convex bow of substrate is typ. < 0.04 mm over plastic surface level of device bottom side

Die Gehäuseabmessungen entsprechen dem Typ TO-273 gemäß JEDEC außer D und D1.
This drawing will meet all dimensions requirement of JEDEC outline TO-273 except D and D1.



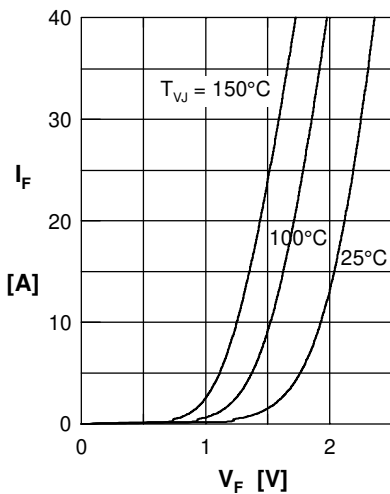
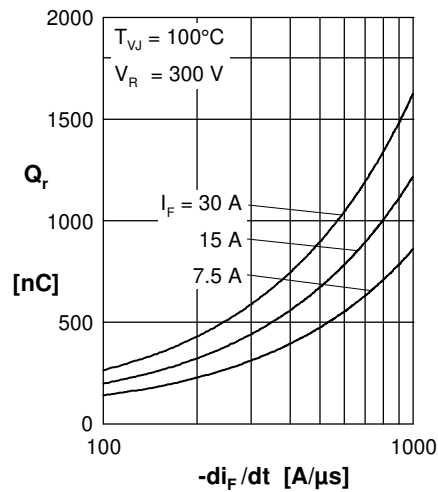
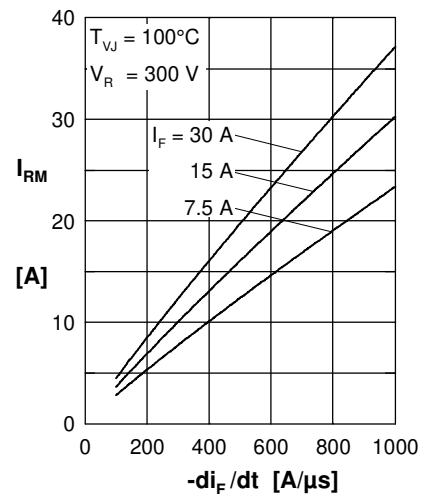
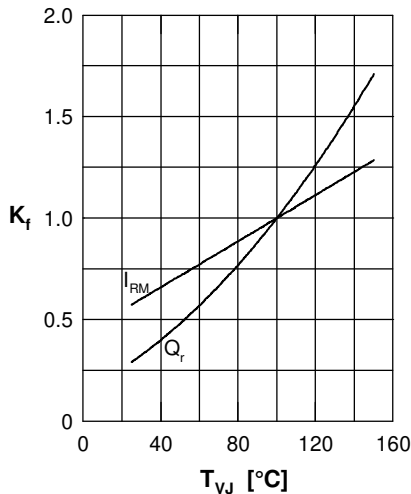
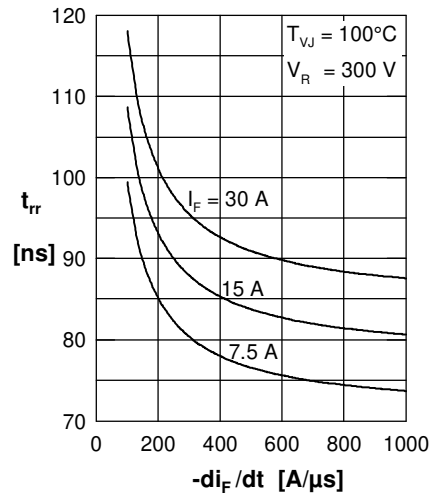
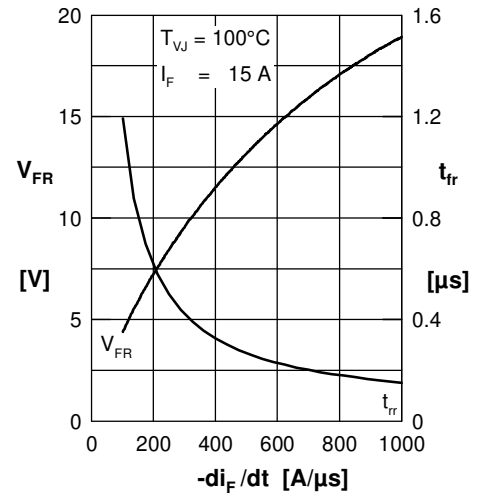
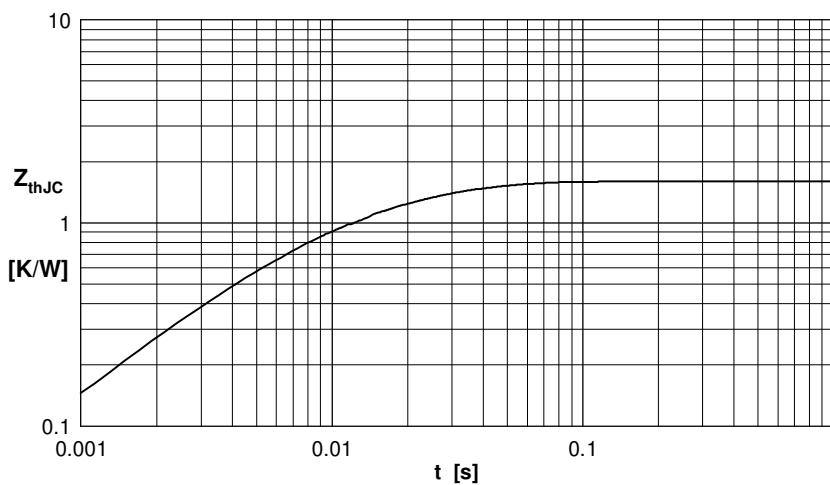
Fast Diode

 Fig. 1 Forward current I_F vs. V_F

 Fig. 2 Typ. reverse recovery charge Q_{rr} versus $-di_F/dt$

 Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

 Fig. 4 Dynamic parameters Q_{rr} , I_{RM} versus T_{VJ}

 Fig. 5 Typ. recovery time t_{rr} versus $-di_F/dt$

 Fig. 6 Typ. peak forward voltage V_{FR} and typ. forward recovery time t_{fr} versus di_F/dt


Fig. 7 Transient thermal impedance junction to case

 Constants for Z_{thJC} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.908	0.0052
2	0.350	0.0003
3	0.342	0.0170